

**Silicon PNP Power Transistors**

**2SA1672**

**DESCRIPTION**

- With TO-3PML package
- Complement to type 2SC4387

**APPLICATIONS**

- Audio and general purpose

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

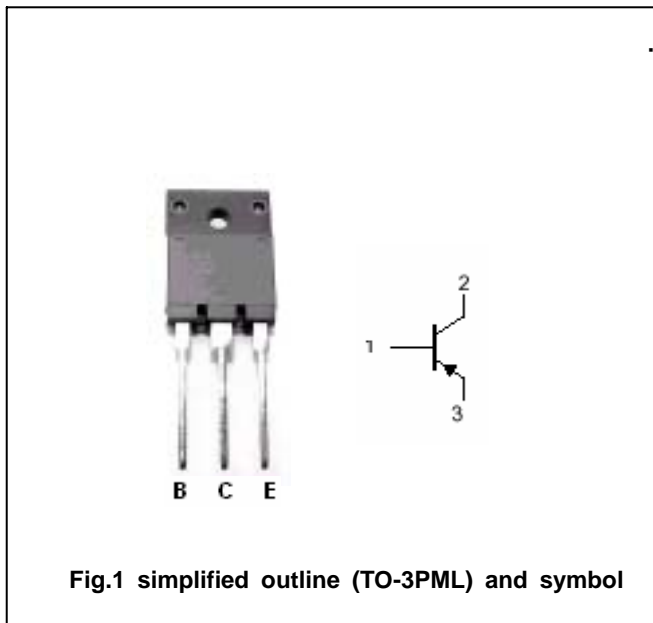


Fig.1 simplified outline (TO-3PML) and symbol

**Absolute maximum ratings(Ta=25 )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-140	V
$V_{CEO}$	Collector-emitter voltage	Open base	-140	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current		-10	A
$I_B$	Base current		-4	A
$P_C$	Collector power dissipation	$T_C=25$	80	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA; I <sub>B</sub> =0	-140			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5 A; I <sub>B</sub> =-0.5 A			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-140V; I <sub>E</sub> =0			-10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V	50		180	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-12V		20		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =-5A; R <sub>L</sub> =12 I <sub>B1</sub> =-I <sub>B2</sub> =-0.5A V <sub>CC</sub> =-60V		0.30		μ s
t <sub>stg</sub>	Storage time			0.90		μ s
t <sub>f</sub>	Fall time			0.20		μ s

◆ h<sub>FE</sub> classifications

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE

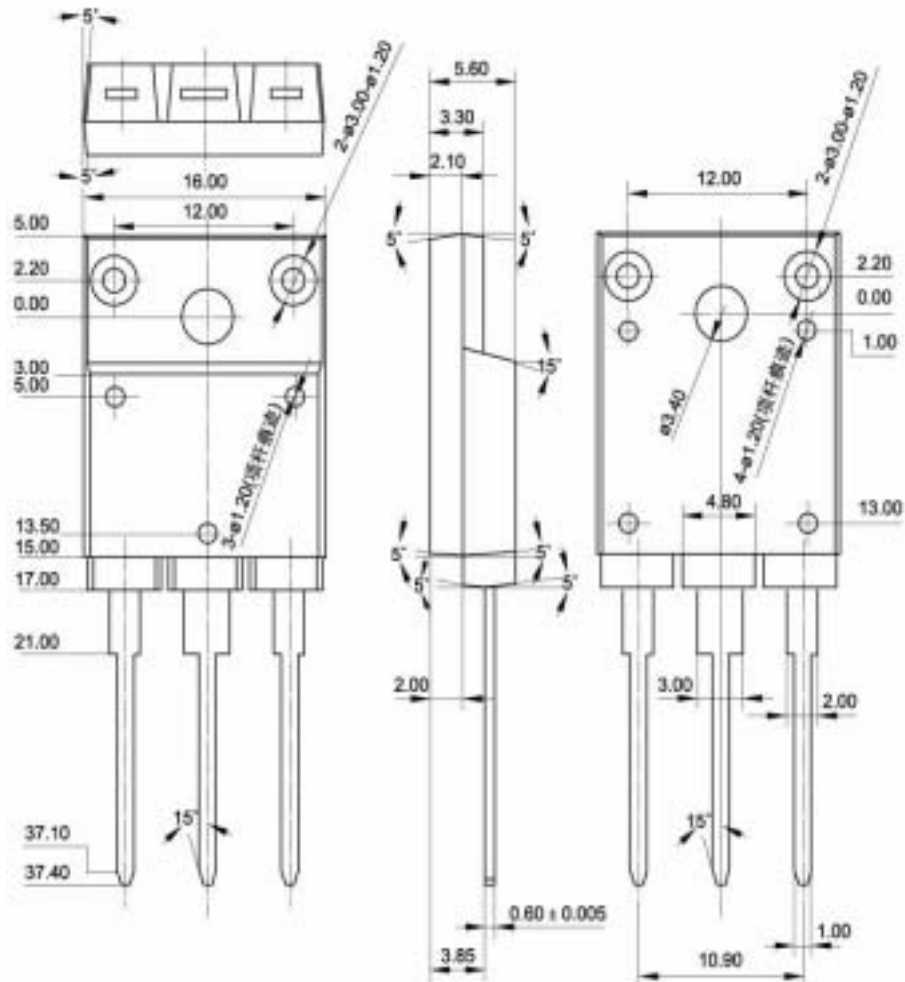


Fig.2 Outline dimensions